

**Amendments to the Claims:**

The following claims will replace all prior versions of the claims in this application (in the unlikely event that no claims follow herein, the previously pending claims will remain):

1. (Currently Amended) A method of forming a metal line layer in a semiconductor device, comprising:
  - depositing a diffusion barrier layer, a metal layer and an anti reflection layer on a semiconductor substrate;
  - depositing an insulating film on the anti reflection layer;
  - depositing and patterning a photosensitive material on the insulating film;
  - etching portions of the insulating film, the anti reflection layer and the metal layer using activated plasma and the photosensitive material as a mask, whereby a portions of side walls of the metal layer are over-etched by plasma ions;
  - removing the photosensitive material;
  - forming a side wall oxide film on the over-etched side walls of the metal layer by reacting the metal layer with ozone; and
  - etching portions of the diffusion barrier layer using the insulating film and the side wall oxide film as an etch mask.
2. (Previously Presented) A method of forming a metal line layer in a semiconductor device according to claim 1, wherein the metal layer is made of aluminum (Al).
3. (Previously Presented) A method of forming a metal line layer in a semiconductor device according to claim 1, wherein the diffusion barrier layer is made of Ti/TiN layer, and the anti reflection layer is made of Ti/TiN layer, and the side wall oxide film is an Al<sub>2</sub>O<sub>3</sub> film.
4. (Currently Amended) A method of forming a metal line in a semiconductor memory device according to claim 1, wherein ~~the~~ the anti reflection layer, the metal layer and the diffusion barrier layer are dry-etched using activated plasma comprising Cl<sub>2</sub>/BCl<sub>3</sub>/N<sub>2</sub> gas.
5. (Canceled)

6. (Previously Presented) A method of forming a metal line in a semiconductor device according to claim 1, wherein the insulating film is a nitride film.

7. (Previously Presented) A method of forming a metal line in a semiconductor device according to claim 1, wherein the insulating film is etched by means of a dry etching process using activated plasma comprising a combination of  $\text{CHF}_3/\text{CF}_4/\text{Ar}$  or  $\text{C}_x\text{F}_y$  (where x, y are natural numbers)/ $\text{O}_2/\text{Ar}$  gas.

8. (Canceled)

9. (Currently Amended) A method of forming a metal line layer in a semiconductor device, comprising:

depositing a first, second and third conductive layers on a semiconductor substrate;

depositing an insulating film on the third conductive layer;

dry etching portions of the insulating film, the third and the second conductive layers using activated plasma, whereby a portions of side walls of the second conductive layer are over-etched by plasma ions;

forming a side wall oxide film on the side walls of the over-etched second conductive layer by reacting the second conductive layer with ozone; and

etching portions of the first conductive layer using the insulating film and the side wall oxide film as an etch mask.

10. (Previously Presented) A method of forming a metal line layer in a semiconductor device according to claim 9, wherein the first conductive layer is made of Ti/TiN layer, the second conductive layer is made of aluminum (Al), and the third conductive layer is made of Ti/TiN layer.

11. (Previously Presented) A method of forming a metal line layer in a semiconductor device according to claim 9, wherein the side wall oxide film is an  $\text{Al}_2\text{O}_3$  film.

12. (Previously Presented) A method of forming a metal line in a semiconductor device according to claim 9, wherein the insulating film is a nitride film.

13. (Previously Presented) A method of forming a metal line in a semiconductor device according to claim 9, wherein the insulating film is etched by means of a dry etching process using activated plasma comprising a combination of  $\text{CHF}_3/\text{CF}_4/\text{Ar}$  or  $\text{C}_x\text{F}_y$  (where x, y are natural numbers)/ $\text{O}_2/\text{Ar}$  gas.

14. (Previously Presented) A method of forming a metal line in a semiconductor memory device according to claim 9, wherein the third and second conductive layers are dry-etched using activated plasma comprising  $\text{Cl}_2/\text{BCl}_3/\text{N}_2$  gas.